

Observation of Coherent Charge-State Mixing in Asymmetric Bloch Transistors

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The reduced switching current of an excited energy-band in a Bloch transistor can be used to detect microwave-induced interband transitions. Spectroscopic measurements of the band-gap are performed by mapping the frequency dependence of the excitation threshold where the microwave photon energy and band-gap are equal. This excitation threshold also provides a probe of charge-state mixing on the island of the transistor. Any asymmetry in the junctions of the transistor makes the coherent mixing of charge-states appear as a finite gap-splitting at the electrostatic degeneracy point between states differing by one excess Cooper-pair on the island. The measured gap-splitting in an asymmetric transistor clearly demonstrates the effect.

The development of nanometer scale tunnel junctions has allowed the control and study of single-electron tunneling in mesoscopic structures [1] [2] [3]. Much of this work has been done using Al/AlO_x/Al tunnel junctions with a magnetic field employed to suppress superconductivity. Investigation of such systems in the superconducting state permits elimination of the dissipation associated with electrons tunneling across a finite voltage drop. These experiments depend heavily upon adequate microwave shielding [4] [5] [6], since the coherent effects of interest are highly noise sensitive. This added difficulty has plagued experimental efforts until recently. However, with proper noise isolation coherent charge-tunneling effects can be observed [7] [8]. One of the most commonly studied systems is the superconducting version of the single-electron transistor, or Bloch transistor [1] [9] [10] [11] [12] [13] [14]. It consists of a pair of small Josephson junctions coupled by a superconducting island (Fig. 1a). An electrostatically coupled gate electrode controls the Coulomb blockade against charge tunneling onto the island. The Hamiltonian describing this system (neglecting interaction with the external environment) can be written,

$$H_0 = E_c(n - Q)^2 - \sum_{i=1,2} E_{Ji} \cos(\varphi_i), \quad (1)$$

where $E_c = e^2/2C_\Sigma$ is the charging energy of the island and E_{J1} , E_{J2} , φ_1, φ_2 are the Josephson coupling energies and phases of the two junctions. The polarization or quasicharge Q on the island is given by $Q = C_g V_g / e + Q'$, where C_g, V_g are the gate capacitance and voltage and Q' is polarization induced by background charge. If the transistor is symmetric, $E_{J1} = E_{J2} \equiv E_J$, the Hamiltonian (Eq. 1) can be simplified in a more natural set of variables, $\varphi \equiv \varphi_1 + \varphi_2$ and $\theta \equiv (\varphi_1 - \varphi_2)/2$, giving,

$$H_0 = E_c(n - Q)^2 - 2E_J \cos(\varphi/2) \cos(\theta). \quad (2)$$

This Hamiltonian consists of the charging energy associated with n excess electrons on the island and an effective coherent coupling, $2E_J \cos(\varphi/2)$, between charge states separated by a single Cooper-pair tunneling. It contains the basic prescription for studying the competition between charging which results in discrete energy states and coherent charge-state mixing which modifies the energy levels. This competition is characterized by the ratio $\alpha \equiv E_J/E_c$. The Hamiltonian (Eq. 2) can be diagonalized in a subspace of charge states $|n\rangle$ where $n = 0, \pm 2, \dots$, or $n = \pm 1, \pm 3, \dots$, depending on the parity of the ground state. At a fixed value of the quasicharge Q , the energy eigenvalues form a unique set of energy bands $E_m(\varphi)|_Q$, each of which is analogous to a Josephson washboard potential. Consequently, each band can support a maximum supercurrent given by,

$$I_{c,m}(Q) = (2e/\hbar) \max\{\partial E_m / \partial \varphi|_Q\}. \quad (3)$$

Sweeping the voltage applied to the gate of the transistor moves the system along the quasicharge axis, producing a characteristic $2e$ -periodic modulation in the critical currents of the bands and the energy-gap between them. Since the minimum energy separation between the ground and first excited band (at fixed Q) occurs at $\varphi = \pi$, it is particularly instructive to consider the energy states $E_m(Q)|_{\varphi=\pi}$ (Fig. 1b). The coherent coupling term is absent in Eq. 2 at

$\varphi = \pi$ and the energy states correspond to those of a superconducting single-electron box (S-SEB) [15] in the limit $E_J \rightarrow 0$ [16]. In the reduced zone picture ($-1 \leq Q \leq 1$), as the gate voltage sweeps the quasicharge, the system follows the lowest energy charging parabola, $E = E_c(n-Q)^2$, with fixed excess charge n on the island. At the zone edge ($Q = 1$), there is a net charge tunneling, incrementing the average charge on the island and taking the system back to the opposite zone edge ($Q = -1$). By tracing the lowest energy charging parabolas within a band, the Q dependence of the average charge on the island at $\varphi = \pi$ is obtained (Figs. 1c - 1d). Clearly, when the coherent coupling is not present, the energy-gap in the reduced zone is just the difference between the charging energies of states differing by one Cooper-pair on the island, $E_G = 4E_c(1-|Q|)$. In particular, the two lowest bands are degenerate at the zone edge.

The situation becomes more interesting when $\varphi \neq \pi$ and the coherent coupling term is present. In this case, coherent mixing of charge states occurs and the degeneracy at the band edges ($Q = \pm 1$) is lifted (dashed lines in Fig. 1b). The effect of the mixing of charge states is also clearly seen in the average charge on the island, where deviations from the S-SEB ($E_J \rightarrow 0$ limit) occur when $\varphi \neq \pi$ (Figs. 1d - 1c). Unfortunately, φ is a dynamical variable which would seem to prevent a systematic study of this coherent effect [8]. However, if the transistor has asymmetric junctions, the degeneracy at $Q = \pm 1$ is again lifted because in this case the coherent coupling terms do not cancel at $\varphi = \pi$. The general expression for the energy gap in an asymmetrical transistor is

$$E_G = \sqrt{(E_{J1} - E_{J2})^2 + (4E_c(1 - |Q|))^2}. \quad (4)$$

Measurements of the band-gap between the lowest bands can be made using the fact that the excited band has a lower critical current than the ground band. Microwave induced excitations resulting in a reduction of the switching current will occur when $E_G \leq \hbar\omega$. According to Eq. 4, for each frequency ω , there is a threshold charge Q_{th} , set by the condition $E_G(Q_{th}) = \hbar\omega$, beyond which no transitions can be excited because the band-gap is larger than a single photon's energy [17]. Measurement of the frequency dependence of Q_{th} constitutes a spectroscopic evaluation of the energy band-gap. Further, at Q_{th} the photon energy is matched to the minimum energy separation which occurs at $\varphi = \pi$, so the system can only be making transitions from this phase region. Thus measurements of the threshold charge probe the energy states of the transistor where it is equivalent to the S-SEB (Fig 1b). While a symmetric transistor is equivalent to the limit $E_J \rightarrow 0$, the asymmetric transistor is analogous to a S-SEB with a coherent coupling given by $E_J = |E_{J1} - E_{J2}|$.

Previous measurements of the band-gap in Bloch transistors were performed on nominally symmetric devices [14]. Figure 2 shows the effects of microwaves on the modulation of the supercurrent for such a device. The critical currents of the bands are calculated using Eq. 3 once the Hamiltonian (Eq. 2) has been diagonalized and the energy bands $E_m(Q, \varphi)$ extracted. The fit to the data is then achieved using an empirically measured relation between the critical currents (I_c) of Josephson junctions [18] and the measured switching currents (I_s). In the low damping limit, there is a theoretical prediction that $I_s \propto I_c^{3/2}$ [13]. Empirically we find a nearly temperature independent exponent, in the range 1.62 to 1.64 between 30 and 100 mK. The vertical bars in Fig. 2 show the expected position of Q_{th} at 28 GHz for the band-gap between the lowest energy bands. The charging energy derived from the band-gap measurement was 0.52 K and the Josephson coupling inferred from the normal state resistance (27.5 k Ω) and the superconducting gap ($\Delta \sim 200 \mu\text{V}$) was 0.54 K, giving the estimate $\alpha = 1$. The best fit using the relation $I_s \propto I_c^{1.63}$ gives $\alpha \sim 0.9$, in reasonable agreement with the estimated value. The microwave power level for the data presented in Figure 2 is rather high, causing a small switching current suppression even above Q_{th} . The dip at $Q = 0$ may be attributed to multiphoton absorption and is suggestive of the presence of the second excited band which is degenerate with the first excited band at this point.

The limited resolution of the measurements near the degeneracy points ($Q = \pm 1$) makes it impossible to detect any gap-splitting caused by coherent charge-state mixing in nominally symmetric transistors where only a small asymmetry is expected due to variance in the fabricated junction sizes. In order to confirm the band-gap (Eq. 4), and observe the gap-splitting produced by coherent charge-state mixing, the asymmetry in the junctions can be made large enough so that $(E_{J1} - E_{J2})/E_c \sim 1$. Then the effect of the gap-splitting should be apparent even far from the degeneracy points at $Q = \pm 1$, making it easily measureable. Figure 3 shows microwave band-gap measurements at two different frequencies for a transistor with a large junction asymmetry by design. The total normal state resistance of the device is $R_n = 18.3 \text{ k}\Omega$. The junction asymmetry can be determined from the asymmetry in the slopes of the voltage modulation produced by the Q dependence of the Coulomb blockade in the normal state [19]. The measured asymmetry for this transistor is 1.9 ± 0.2 although the designed junction sizes were $0.01 \mu\text{m}^2$ and $0.025 \mu\text{m}^2$. Thus the estimated Josephson coupling energies are $E_{J1} = 1.19 \text{ K}$ and $E_{J2} = 0.62 \text{ K}$. The charging energy is not easily measurable for transistors with $R_n \leq R_k = h/e^2 = 25.8 \text{ k}\Omega$, so it is treated as a fitting parameter to be compared with estimates based on the designed junction sizes and a previously measured specific capacitance $C_\square = 43 \text{ fF}/\mu\text{m}^2$ [14]. Figure 4 shows the results of the band-gap measurement. The error bar at $Q = 1$ is not determined by a

direct measurement of Q_{th} , but rather by decreasing the microwave frequency until no Q dependent switching current suppression is seen at any input power level up to that which causes Q independent suppression. The gap-splitting at $Q = 1$ due to coherent charge-state mixing is evident and the fit to Eq. 4 is reasonably good using the inferred Josephson coupling energies and a charging energy of 0.6 K. The fit charging energy compares well with the estimate based on the designed junction sizes (0.62 K) even though the junction asymmetry indicates that the ratio of junction areas differs from the designed value by $\sim 25\%$. This probably indicates that most of the size deviation has occurred in the smaller junction.

In summary, microwave induced interband transitions provide a spectroscopic probe of the band-gap in Bloch transistors. Transitions which occur at the threshold charge where the band-gap and photon energy are equal can only take place in a limited phase region near $\varphi = \pi$, where the behavior of the transistor is simply related to mixing of charge states on the island. Symmetric transistors which have no coherent coupling in this region, have a degeneracy in the energy bands. In asymmetric transistors the coherent coupling between charge-states differing by one excess Cooper-Pair on the island, lifts the degeneracy. The data presented clearly show this coherence induced gap-splitting and are in quantitative agreement with the expected band-gap over the measured range of quasicharge Q .

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FIG. 1. a) Schematic of a Bloch transistor which is characterized by the Josephson coupling energies of the junctions (E_{J1} , E_{J2}) and the charging energy of the island capacitance ($C_\Sigma = C_1 + C_2 + C_g$). b) Energy states for a symmetric transistor at $\varphi = \pi$ (solid lines) where there is no coherent coupling and $\varphi \neq \pi$ (dashed lines) where coherent coupling lifts the degeneracy at the reduced zone edges. c) and d) Calculated average charge on the island of a transistor with $\alpha = 1.5$ in c) the ground band ($m=0$) and d) the first excited band ($m=2$).

FIG. 2. The effect of 28 GHz irradiation on the switching current modulation of a nominally symmetric transistor. The raw switching data at 30 mK, with and without microwaves, are shown overlaid with the theoretical prediction. An empirically measured relation has been used to convert the calculated critical currents to switching currents - see text for details.

FIG. 3. Band-gap measurements at a) 24 GHz and b) 32 GHz. The data were taken at 80 mK and sets with and without irradiation are shown in each panel. The lower traces are the differences between the averaged switching distributions of the sets (offset and scaled for clarity). The vertical bars represent the threshold charge (Q_{th}) determined from several modulation periods.

FIG. 4. The measured frequency dependence of the threshold charge Q_{th} for an asymmetric transistor. The error bars are attributable primarily to fluctuations in the background charge (Q') and are estimated based on measurements over several modulation periods. The solid line is a fit to Eq. 4 using the measured junction asymmetry while the dashed line is the expected fit for a symmetric transistor with equivalent charging energy.







